

## **UTV120**

12 Watts, 26.5 Volts, Class A UHF Television - Band IV & V

### **GENERAL DESCRIPTION**

The UTV 120 is a COMMON EMITTER transistor capable of providing 12 Watts Peak, Class A, RF Output Power over the band 470 - 860 MHz. The transistor includes double input prematching for full broadband capability. Gold Metalization and Diffused Ballasting are used to provide high reliability and supreme ruggedness.

### **ABSOLUTE MAXIMUM RATINGS**

Maximum Power Dissipation @ 25°C 80 Watts

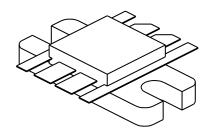
### **Maximum Voltage and Current**

BVcesCollector to Emitter Voltage45 VoltsBVceoCollector to Emitter Voltage28 VoltsBVeboEmitter to Base Voltage4 VoltsIcCollector Current3.5 Amps

### **Maximum Temperatures**

Storage Temperature  $-65 \text{ to} + 150 ^{\circ}\text{C}$  Operating Junction Temperature  $+200 ^{\circ}\text{C}$ 

# CASE OUTLINE 55JT, STYLE 2



### ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg IMD¹ VSWR₁	Power Out - Pk Sync Power Input Power Gain Intermodulation Distortion Load Mismatch Tolerance	F = 470 - 860 MHz Vcc = 26.5 Volts Ic = 1.7 Amps Pref = 12 Watts F = 860 MHz	12 8.9	9.5	1.55 -52 3:1	Watts Watts dB dB

LVceo <sup>2</sup> BVces <sup>2</sup> BVebo <sup>2</sup> h <sub>FE</sub> <sup>2</sup> Cob <sup>2</sup>	Collector to Emitter Breakdown Collector to Base Breakdown Emitter to Base Breakdown Current Gain	Ic = 65 mA Ic = 25 mA Ie = 10 mA Vce = 5 V, 500 mA Vcb = 26 V, F = 1	28 45 4 10	23		Volts Volts Volts
θjc	Output Capacitance Thermal Resistance	MHz Tc = 25°C		23	1.6	°C/W

Note 1: F1=860 MHz, F2=863.5 MHz, F3=864.5 Mhz

European test method, Vision = -8dB, Sideband= -16dB, Sound = -7 dB

Note 2: Per side

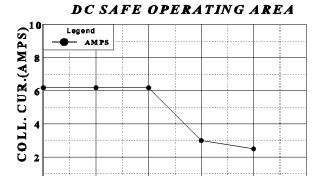
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### **UTV120**

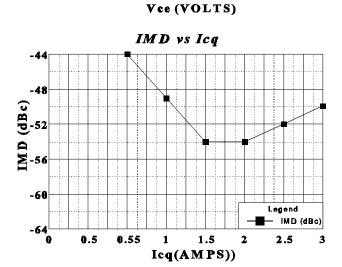




18

26.5

30



# SER. REACT. (OHMS)

FREQUENCY (MHz)

700

800

900

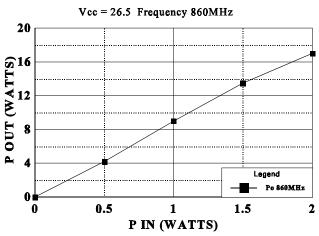
600

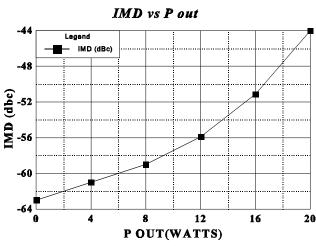
400

500

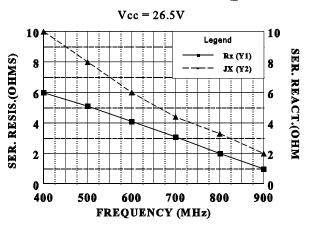
SERIES INPUT IMPEDANCE vs FREQUENCY

### **POWER OUTPUT vs POWER INPUT**





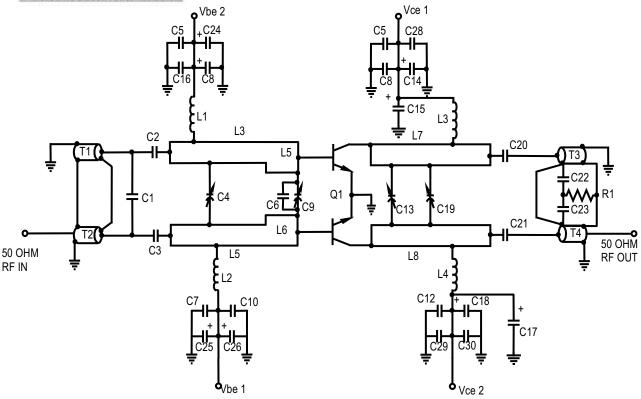
### SERIES LOAD IMPEDANCE vs FREQUENCY



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# **UTV-120**



### **CAPACITORS**

C1,C6=4.7 pF ATC series A
C2,C3,C20,C21=33 pF ATC series A
C4,C9=1.2-3.5 pF film diel. trimmer
C5,C7,C11,C12=0.01 mF, 50 V Tantalum
C8,C15,C17,C25=1 mF, 50 V Tantalum
C10,C16,C27,C12=0.1 mF 50 V disc ceramic
C13=0.6-6 pF piston trimmer
C19=0.35-3.5 pF piston trimmer
C18,C24,C14,C26=10 mF, 50 V
C28,C30=0.001 mF, 50 V disc ceramic
C31=100 mF, 50 V electrolytic

### RESISTORS

R1=10 Ohm, 1/2 W Carbon R2,R6=500 Ohm potentiometer R3,R7=4.7K Ohm, 3W, 1% Carbon R4,R8=1 Ohm, 3W, 1% Carbon film R5,R9=47 Ohm, 1/4W Carbon film DIODES CR1,CR2=IN4148

### **INDUCTORS**

L1,L2=0.46 microHenry molded L3,L4=1 turn #18 magnet wire on a 0.325" form

### TRANSISTORS

Q1=GHz UTV-120 Q2,Q3=MJE172

### **TRANSFORMERS**

T1,T2,T3,T4=50 Ohm semi-rigid coax cable (0.056" X 1.1") soldered to 0.035" X 1.1" microstrip

# R2 + IC31 R4 R6 R8 CRT Q2 Vce 1 CR2 Q3 Vbe 1 Vbe 2

MICROSTRIPLINES L3,L4=0.075" X 0.65" L5,L6=0.120" X 0.31" L7,L8=0.120" X 1.33"